



#### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
60V	$2\Omega$ @ $V_{GS} = 10V$	380mA
000	$3\Omega$ @ $V_{GS} = 5V$	310mA

### **Description**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

- Motor Control
- Power Management Functions
- Backlighting

### **Features and Benefits**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

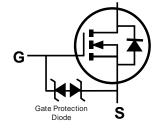
#### **Mechanical Data**

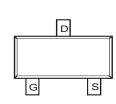
- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (Approximate)





**SOT323** 





Top View

**Equivalent Circuit** 

Top View

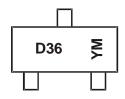
### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMN63D1LW-7	SOT323	3000/Tape & Reel
DMN63D1LW-13	SOT323	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



D36 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: B = 2014) M = Month (ex: 9 = September)

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	В	С	D	Е	F	G	Н		J	K	L	М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



## **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V <sub>DSS</sub>	60	V	
Gate-Source Voltage		$V_{GSS}$	±20	V	
			I <sub>D</sub>	380 300	mA
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	l <sub>D</sub>	430 340	mA		
Maximum Continuous Body Diode Forward Current	Is	0.5	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	b) (Note 6)		I <sub>DM</sub>	1.2	А

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P <sub>D</sub>	310	mW
Ste		В	411	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<5s	$R_{\theta JA}$	371	C/VV
Total Power Dissipation (Note 6)		P <sub>D</sub>	410	mW
Stead		В	311	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<5s	$R_{\theta JA}$	257	C/VV
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C

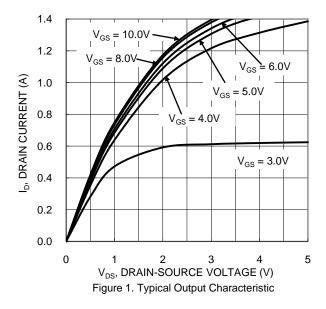
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

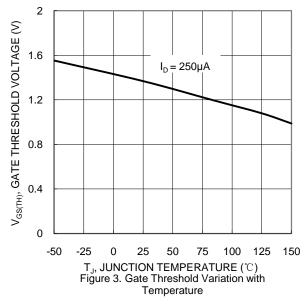
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V, I_{D} = 10\mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1.0	μΑ	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0	1.6	2.5	V	$V_{DS} = 10V, I_{D} = 1mA$
Static Drain-Source On-Resistance	ם		_	2.0	Ω	$V_{GS} = 10V, I_D = 0.5A$
Static Diani-Source On-Resistance	R <sub>DS(ON)</sub>		_	3.0	12	$V_{GS} = 5V, I_D = 0.05A$
Forward Transfer Admittance	Y <sub>fs</sub>	80	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage	$V_{SD}$	_	0.75	1.1	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C <sub>iss</sub>	_	30	_	pF	
Output Capacitance	Coss	_	4.2	_	pF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	2.9	_	pF	1 – 1.00112
Gate Resistance	$R_g$	_	133	_	Ω	$f = 1MHz$ , $V_{GS} = 0V$ , $V_{DS} = 0V$
Total Gate Charge	$Q_g$		304	_	рС	
Gate-Source Charge	Q <sub>gs</sub>	_	203	_	рС	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_{D} = 250mA$
Gate-Drain Charge	Q <sub>gd</sub>	_	84	_	рС	1D = 230111A
Turn-On Delay Time	t <sub>D(ON)</sub>		3.9		ns	
Turn-On Rise Time	t <sub>R</sub>		3.4		ns	V <sub>DD</sub> = 30V, V <sub>GS</sub> = 10V,
Turn-Off Delay Time	t <sub>D(OFF)</sub>		15.7		ns	$R_G = 25\Omega$ , $I_D = 200mA$
Turn-Off Fall Time	t <sub>F</sub>		9.9		ns	

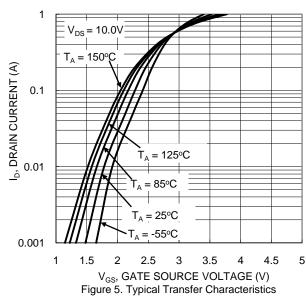
Notes:

- Device mounted on FR-4 PCB, with minimum recommended pad layout.
   Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
   Short duration pulse test used to minimize self-heating effect.
   Guaranteed by design. Not subject to product testing.









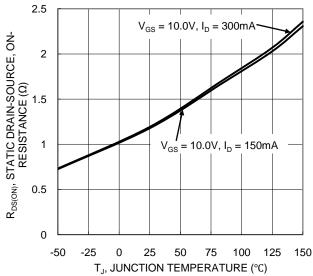
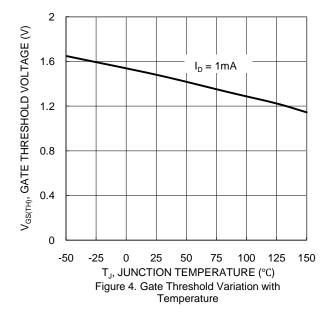
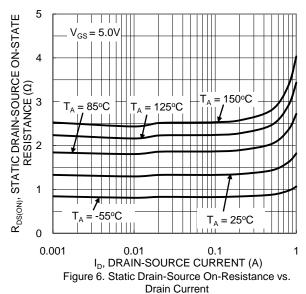
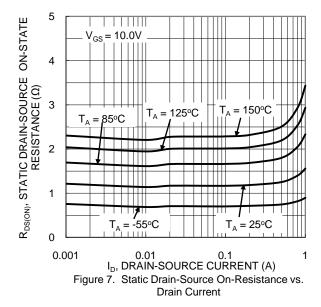


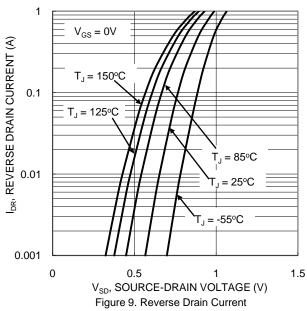
Figure 2. On-Resistance Variation with Temperature

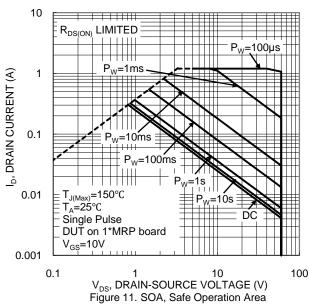


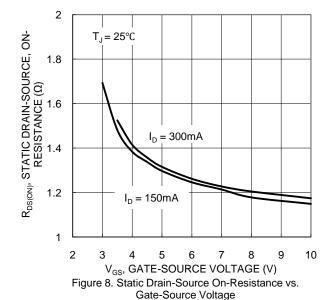






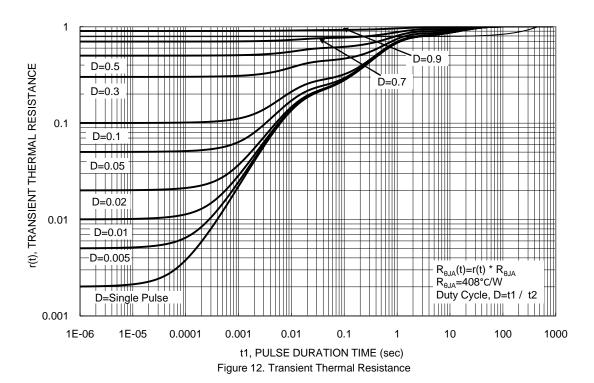






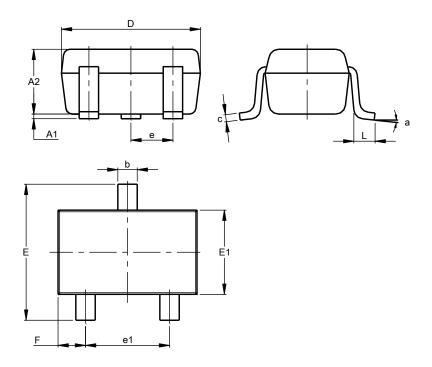
50 45 f=1MHz C<sub>T</sub>, JUNCTION CAPACITANCE (pF) 40 35  $C_{\rm iss}$ 30 25 20 15  $C_{rss}$ 10 5 0 0 10 15 20 25 30 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 10. Typical Junction Capacitance





# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

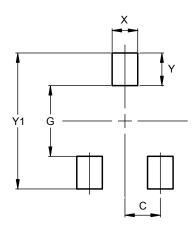


SOT323								
Dim	Min	Max	Тур					
A1	0.00	0.10	0.05					
A2	0.90	1.00	0.95					
b	0.25	0.40	0.30					
С	0.10	0.18	0.11					
D	1.80	2.20	2.15					
Е	2.00	2.20	2.10					
E1	1.15	1.35	1.30					
е	C	).650 B	SC					
e1	1.20	1.40	1.30					
F	0.375	0.475	0.425					
L	0.25	0.40	0.30					
а	a 8°							
All Dimensions in mm								



### **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

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